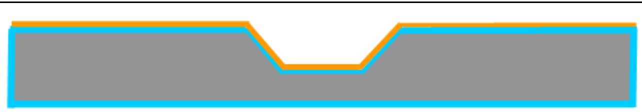
520.495/530.495/580.495 Microfabrication Laboratory

Flow Cytometer **Laboratory Assignment 5** **Metal Evaporation**	

This week we will continue the flow cytometer process by deposition (E-beam) of aluminum in the electrode areas. After the thermal evaporation we will spin photoresist on the fresh material to get ready for next week's photolithography.

I. PRELAB ASSIGNMENT:

1. What is the electrical resistivity, density and melting temperature of Aluminum, Copper and Gold?

2. Among aluminum, gold and copper, which has the best electrical properties? Copper is commonly used in IC taking the position of aluminum, which was employed before a decade. Which is the reason for copper preference but not gold and aluminum.

II. LAB WORK:

Preliminaries:

1. Transfer wafers with tweezers, try to grasp the wafer at the same place each time, usually at the flat edge.
2. All processing and the cleaning procedures (except using spin/rinse/dryer) should be done in the hood. Aprons, protective sleeves, gloves, face shield, lab coat, and goggles must be worn during cleaning procedures. Wear plastic disposable gloves **always**.

Task #1: Evaporation:

1. If not clean, use clean wipes and alcohol to clean the evaporator bell where aluminum is deposited during the previous evaporation cycle.
2. Place wafers onto the stage of the evaporator.
3. Load 1/2" pieces of Al wire into the "tungsten boat".
4. Pump down evaporator following instructions provided.
5. When a pressure of approximately 10^{-6} torr is reached, use the Variac to **slowly** increase the current through the boat. Aluminum should melt and will begin to cover the wafers. If you increase the current too fast, the aluminum will splatter out of the "boat"! Continue the deposition until aluminum disappears from the "boat" (it takes between 5 and 10 mins).
6. Let the evaporator come to ambient pressure following instructions of the lab assistants and take the wafers out of the evaporator bell.

Task #2: Photoresist Deposition:

1. Set the photoresist spinner RPM at 2000 RPM with acceleration in approximately 5 secs and the timer to 60 secs for spinning.

Lab procedure prepared by H. Vo and A.G. Andreou, Fall 2003, and revised by H. Vo, T. Yeh, M. Ho and A.G. Andreou, Fall 2007, C. Sapsanis Fall 2018.

2. Make sure that the vacuum is on after centering the wafer on the chuck. You can do that by gently trying to push the wafer off the chuck using the tweezers.
3. Carefully withdraw approximately 1 ml of positive photoresist **SJR5740** from the bottle into the pipette.
4. Dispense photoresist on to the wafer slowly and try not to create any air bubbles.
5. Double check that the vacuum is on and cover the spinner. Now start spinning (60 secs at 2000 RPM)
6. Soft bake wafers on hotplate at approximately 105 °C for 7 mins.
7. Carefully get the wafer off the hot plate and place them in their carriage to be stored (in a dark place) until next week.

III. POSTLAB ASSIGNMENT:

1. Based on today's lab work, how thick of an aluminum layer did you deposit? Compare this with the thickness as measured by the gauge on the machine.

2. What photoresist did we use today? Based on the spin-on procedure, how thick of a photoresist layer do you think you have on your wafer?

3. What are the differences between positive and negative photoresist? Please name a couple of positive and negative resists that are currently being used by the semiconductor industry. Who are their manufactures?

4. Is the thickness of the photoresist the same everywhere on the wafer? If not, what area has the thickest photoresist (draw a cross section of your device to illustrate this.)

5. Draw important cross sections of your device after this lab.

6. Why did we wait for the pressure of the evaporation chamber to go down to 1×10^{-6} torr before we initiate the evaporation process?